

1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 plastic package intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing with low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- Air conditioner indoor fan
- General purpose low power motor control
- General purpose switching and phase control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{lead}} \leq 51\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	12.5	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	-	13.7	A
T_{j}	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G+; $T_{\text{j}} = 25\text{ °C}$; Fig. 7	-	0.4	3	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G-; $T_{\text{j}} = 25\text{ °C}$; Fig. 7	-	1.3	3	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2- G-; $T_{\text{j}} = 25\text{ °C}$; Fig. 7	-	1.4	3	mA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7		-	3.8	7	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9		-	1.3	5	mA
V_T	on-state voltage	$I_T = 1.4\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10		-	1.2	1.5	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; $R_{GT1(ext)} = 1\text{ k}\Omega$; Fig. 12		10	20	-	V/ μs
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $dI_{com}/dt = 0.5\text{ A/ms}$; $I_T = 1\text{ A}$		2	-	-	V/ μs

5. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BT131-800	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

6. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{lead}} \leq 51\text{ }^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3		-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; Fig. 4; Fig. 5		-	12.5	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 16.7\text{ ms}$		-	13.7	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; sine-wave pulse		-	0.78	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{G}} = 6\text{ mA}$		-	50	$\text{A}/\mu\text{s}$
				-	50	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 14\text{ mA}$		-	10	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 6\text{ mA}$		-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current			-	2	A
P_{GM}	peak gate power			-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period		-	0.1	W
T_{stg}	storage temperature			-40	150	$^{\circ}\text{C}$
T_{j}	junction temperature			-	125	$^{\circ}\text{C}$

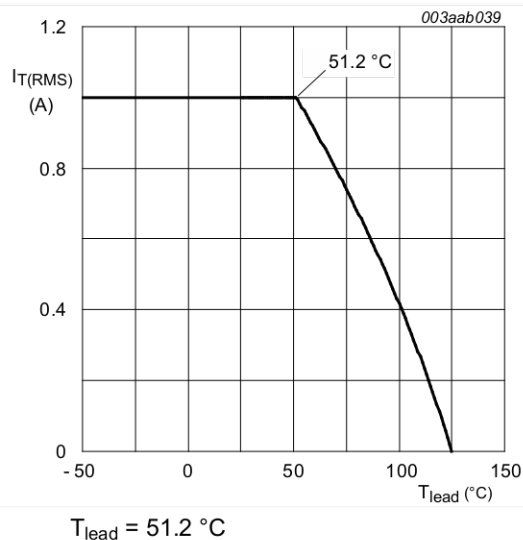


Fig. 1. RMS on-state current as a function of lead temperature; maximum values

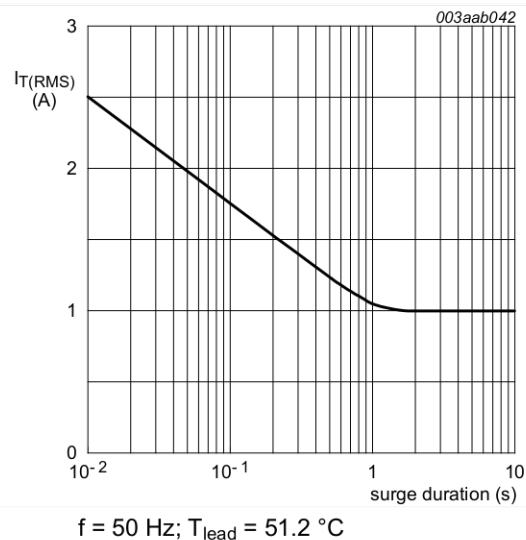
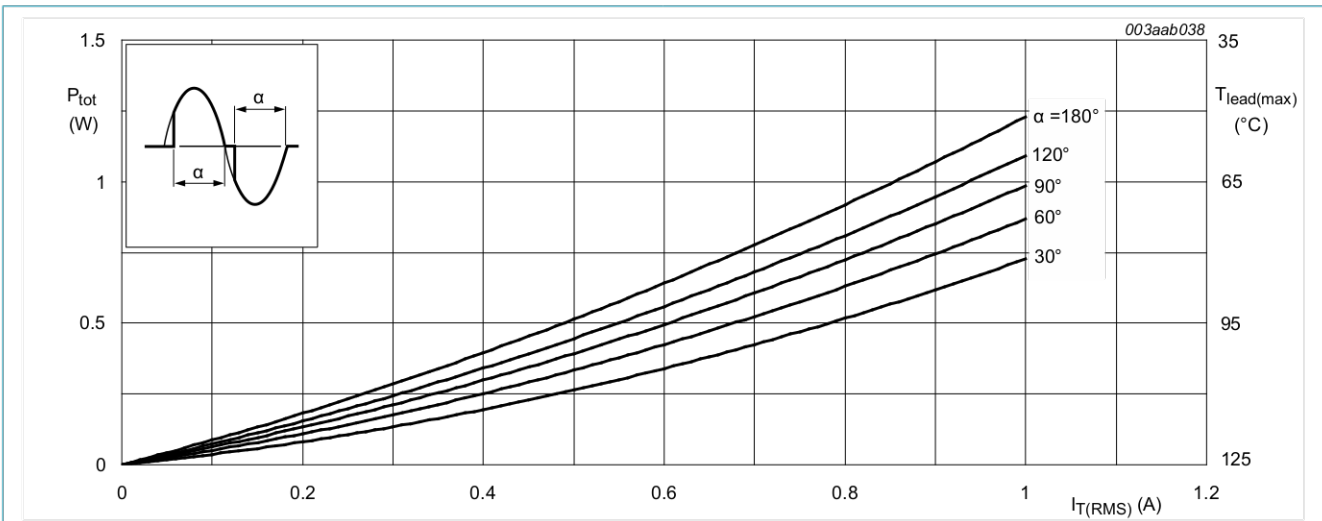
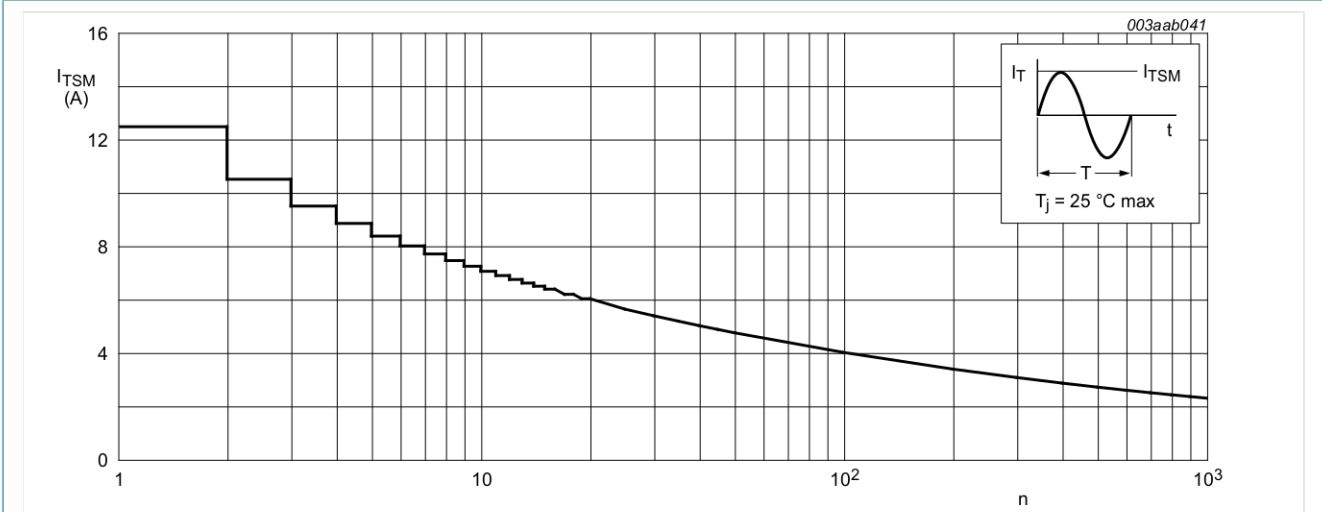


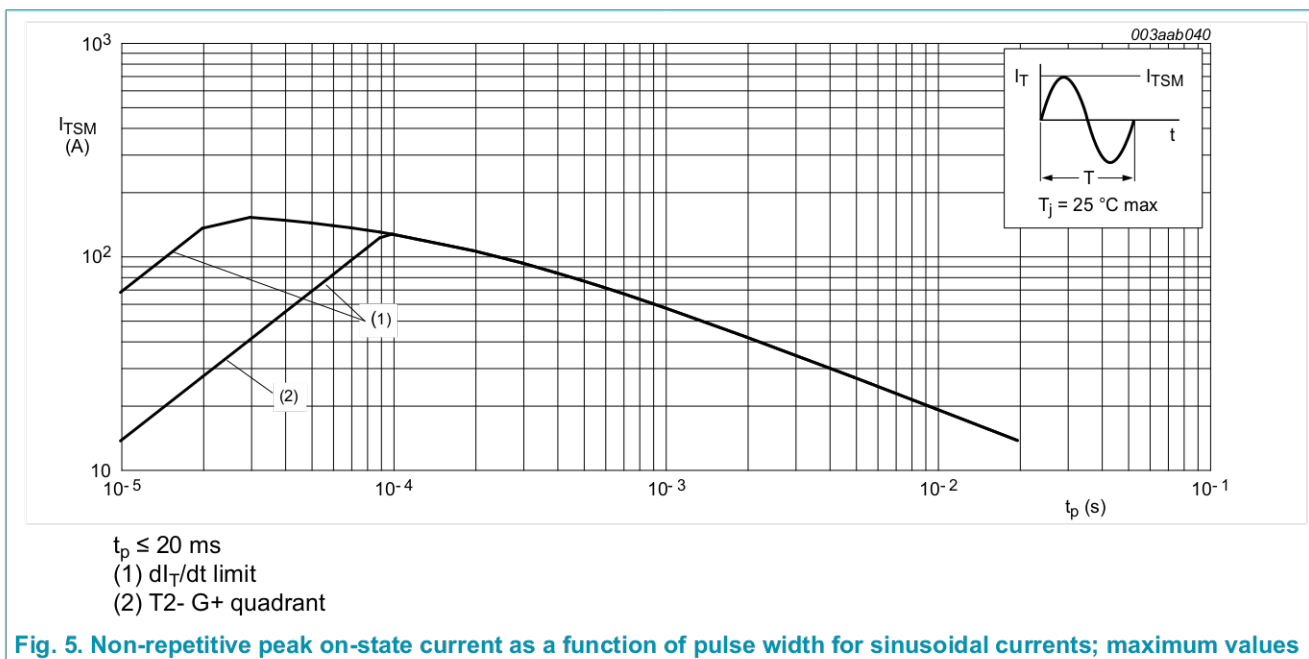
Fig. 2. RMS on-state current as a function of surge duration; maximum values



α = conduction angle
Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



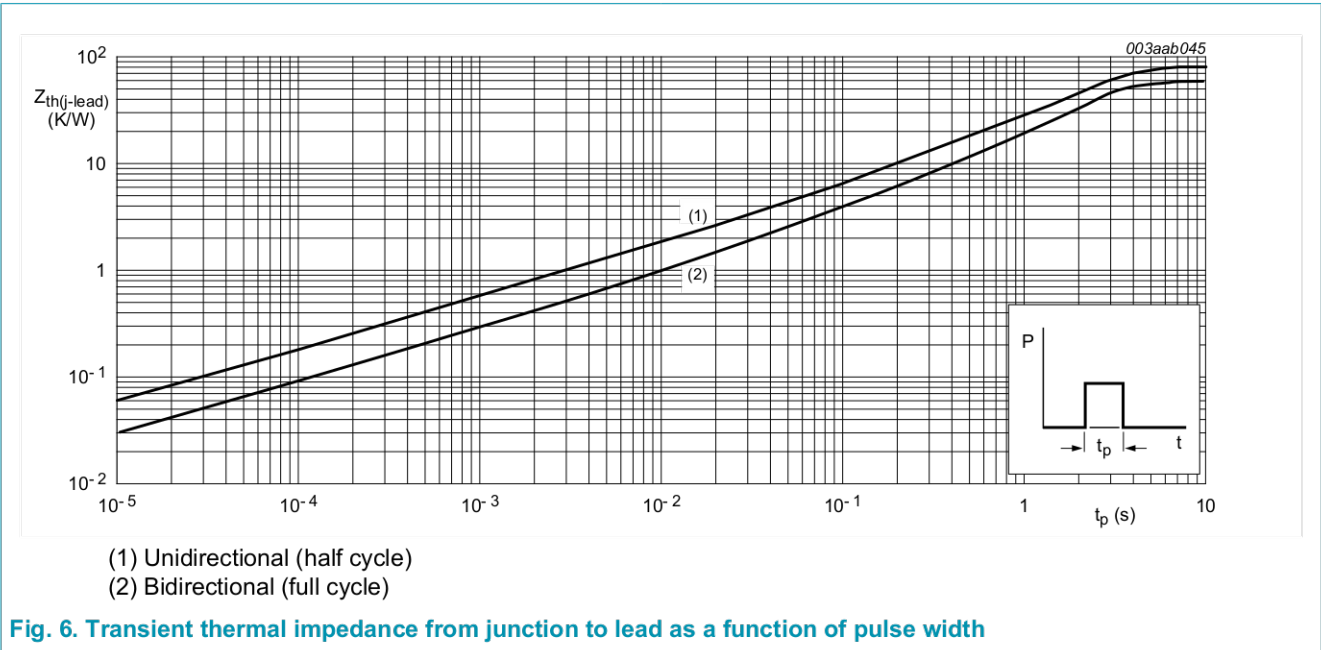
$f = 50\text{ Hz}$
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



7. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
		half cycle; Fig. 6	-	-	80	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



8. Characteristics

Table 5. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7		-	0.4	3	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7		-	1.3	3	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7		-	1.4	3	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7		-	3.8	7	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8		-	1.2	5	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8		-	4	8	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8		-	1	5	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8		-	2.5	8	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9		-	1.3	5	mA
V_T	on-state voltage	$I_T = 1.4\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10		-	1.2	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 11		-	0.7	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ }^\circ\text{C}$; Fig. 11		0.2	0.3	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$		-	0.1	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; $R_{GT1(ext)} = 1\text{ k}\Omega$; Fig. 12		10	20	-	V/ μs
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $dI_{com}/dt = 0.5\text{ A/ms}$; $I_T = 1\text{ A}$		2	-	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 1.5\text{ A}$; $V_D = 800\text{ V}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$		-	2	-	μs

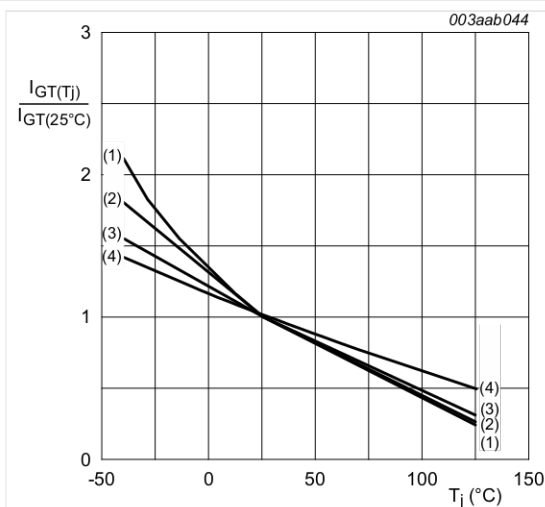


Fig. 7. Normalized gate trigger current as a function of junction temperature

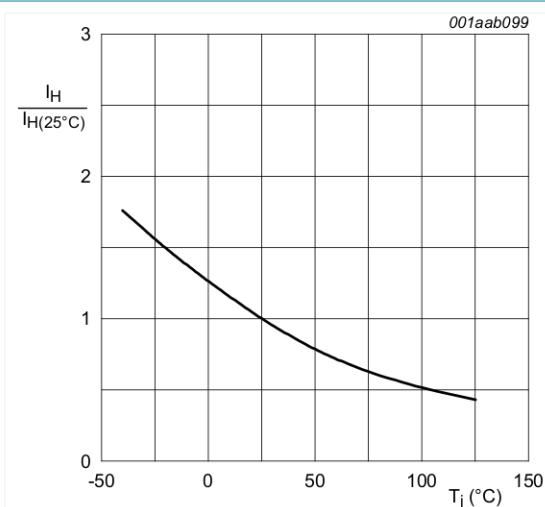


Fig. 9. Normalized holding current as a function of junction temperature

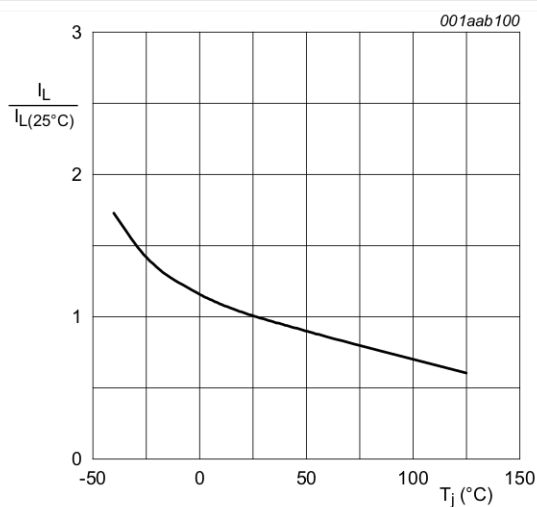
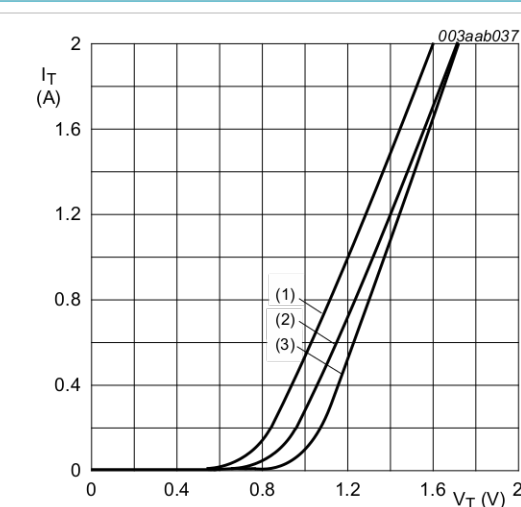


Fig. 8. Normalized latching current as a function of junction temperature



$V_o = 0.92 \text{ V}$; $R_s = 0.4 \Omega$

(1) $T_j = 125^\circ\text{C}$; typical values

(2) $T_j = 125^\circ\text{C}$; maximum values

(3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

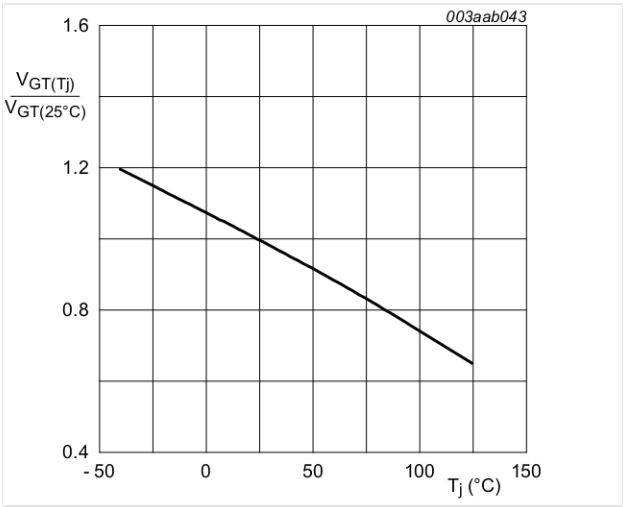


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

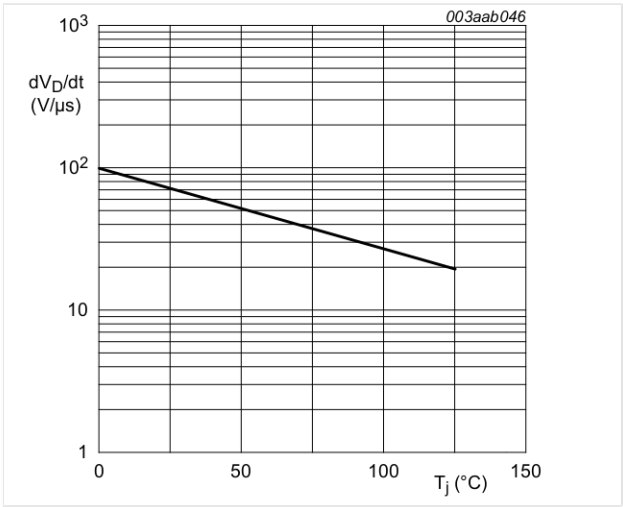


Fig. 12. Rate of rise of off-state voltage as a function of junction temperature; typical values

9. Package outline

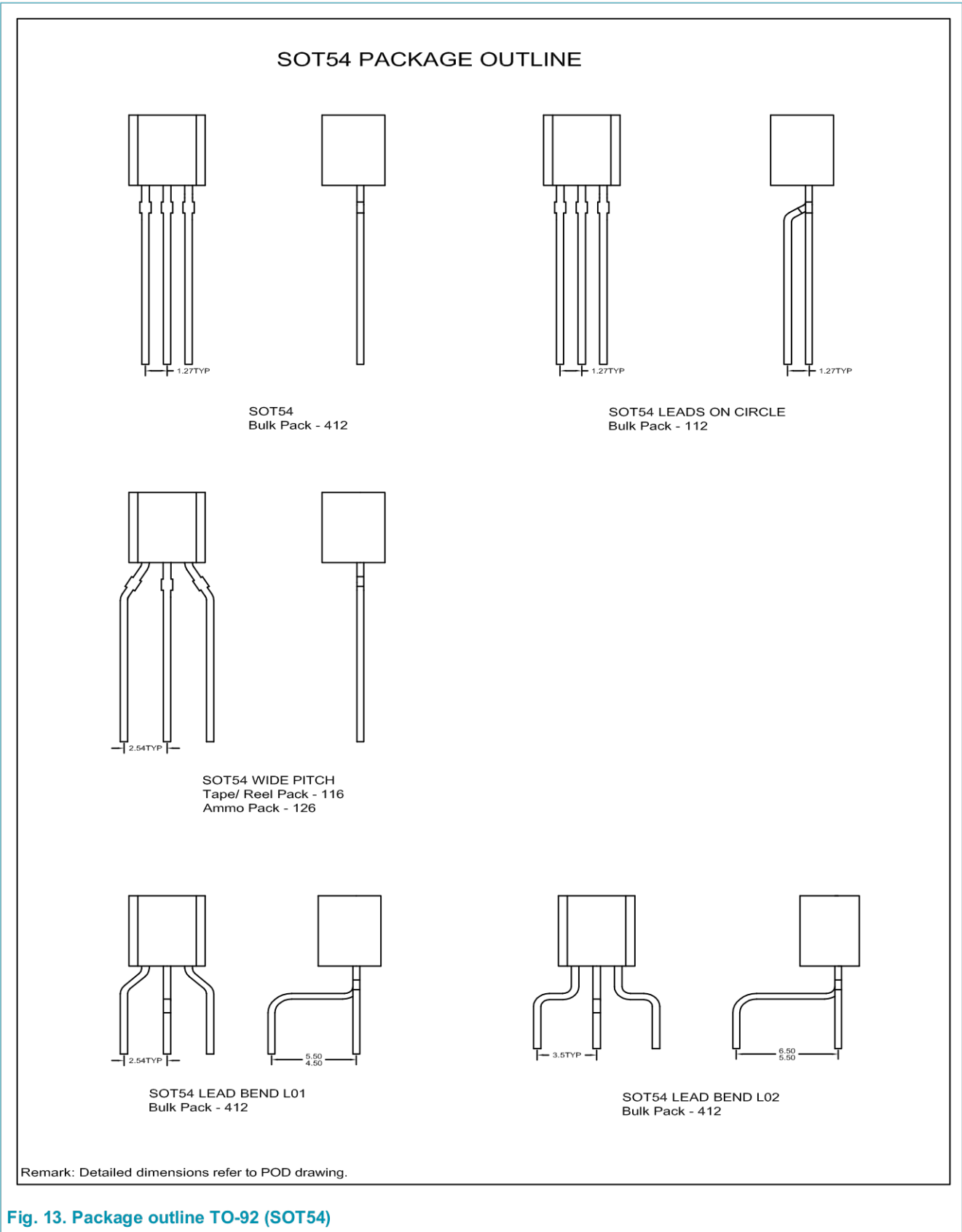


Fig. 13. Package outline TO-92 (SOT54)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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11. Contents

1. General description.....	1
2. Features and benefits.....	1
3. Applications.....	1
4. Quick reference data.....	1
5. Ordering information.....	2
6. Limiting values.....	3
7. Thermal characteristics.....	6
8. Characteristics.....	7
9. Package outline.....	10
10. Legal information.....	11

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